PARADIGM®

PDM41096

4 Megabit Static RAM
512K x 8-Bit

Features

- High speed access times
  Com'l: 15, 17, 20 and 25 ns
  Ind: 17, 20 and 25 ns
- Low power operation (typical)
  - PDM41096SA
  Active: 400 mW
  Standby: 150 mW
  - PDM41096LA
  Active: 350 mW
  Standby: 100 mW
- TTL compatible inputs and outputs
- Single +5V (±10%) power supply
- Three-State output
- Packages
  Plastic SOJ (400 mil) - SO

Description

The PDM41096 is a high-performance CMOS static RAM organized as 524,288 x 8 bits. This product is produced in Paradigm's proprietary CMOS technology which offers the designer the highest speed parts. Writing is accomplished when the write enable ($\overline{WE}$) and the chip enable ($\overline{CE}$) inputs are both LOW. Reading is accomplished when $\overline{WE}$ remains HIGH and $\overline{CE}$ and $\overline{OE}$ are both LOW.

The PDM41096 operates from a single +5V power supply and all the inputs and outputs are fully TTL compatible. The PDM41096 comes in two versions, the standard power version PDM41096SA and a low power version the PDM41096LA. The two versions are functionally the same and only differ in their power consumption.

The PDM41096 is available in a 36-pin 400 mil plastic SOJ package.

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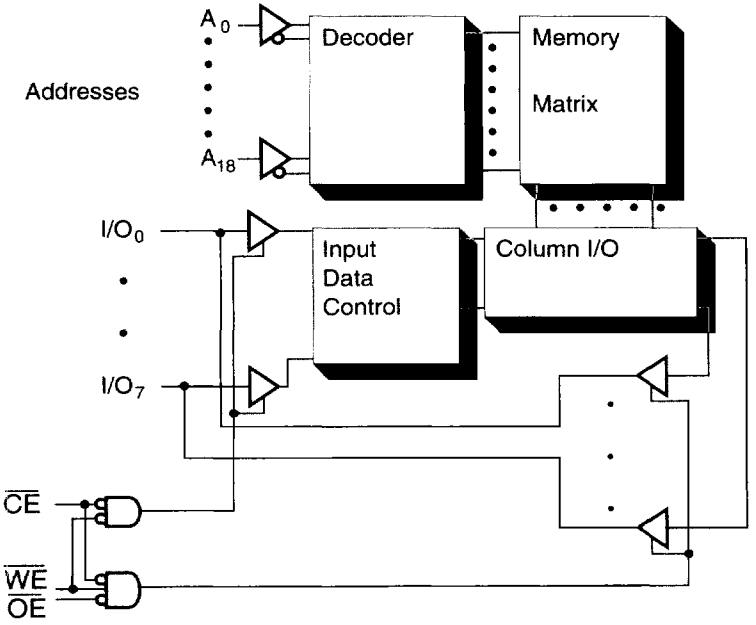
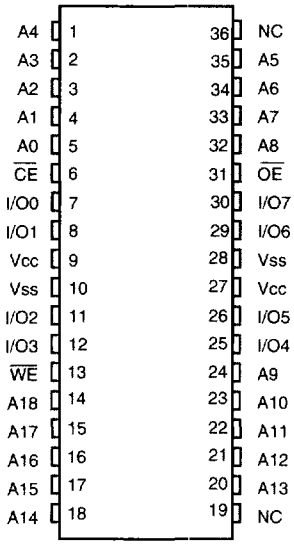
Functional Block Diagram



Pin Configuration
36-Pin SOJ



Pin Description

Name	Description
A18-A0	Address Inputs
I/O7-I/O0	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
NC	No Connect
V_{SS}	Ground
V_{CC}	Power (+5V)

Truth Table(1)

$\overline{OE}$	$\overline{WE}$	$\overline{CE}$	I/O	MODE
X	X	H	Hi-Z	Standby
L	H	L	D_{OUT}	Read
X	L	L	D_{IN}	Write
H	H	L	Hi-Z	Output Disable

NOTE: 1. H = V_{IH}, L = V_{IL}, X = DON'T CARE

Absolute Maximum Ratings (1)

Symbol	Rating	Com'l.	Ind.	Unit
V_{TERM}	Terminal Voltage with Respect to V_{SS}	–0.5 to +7.0	–0.5 to +7.0	V
T_{BIAS}	Temperature Under Bias	–55 to +125	–65 to +135	°C
T_{STG}	Storage Temperature	–55 to +125	–65 to +150	°C
P_T	Power Dissipation	1.4	1.4	W
I_{OUT}	DC Output Current	50	50	mA
T_j	Maximum Junction Temperature (2)	125	125	°C

NOTE: 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. Appropriate thermal calculations should be performed in all cases and specifically for those where the chosen package has a large thermal resistance (e.g., TSOP). The calculation should be of the form: $T_j = T_a + P * \theta_{ja}$ where T_a is the ambient temperature, P is average operating power and θ_{ja} the thermal resistance of the package. For this product, use the following θ_{ja} value:

   SOJ: 59° C/W

Recommended DC Operating Conditions

Symbol	Description	Min.	Typ.	Max.	Unit
V_{CC}	Supply Voltage	4.5	5.0	5.5	V
V_{SS}	Supply Voltage	0	0	0	V
Industrial	Ambient Temperature	–40	25	85	°C
Commercial	Ambient Temperature	0	25	70	°C

DC Electrical Characteristics (V_{CC} = 5.0V ± 10%)

Symbol	Parameter	Test Conditions		PDM41096SA Min.	PDM41096SA Max.	PDM41096LA Min.	PDM41096LA Max.	Unit
I_{LI}	Input Leakage Current	V_{CC} = MAX., V_{IN} = V_{SS} to V_{CC}	Com'l	–5	5	–5	5	µA
I_{LO}	Output Leakage Current	V_{CC} = MAX., $\overline{CE}$ = V_{IH}, V_{OUT} = V_{SS} to V_{CC}	Com'l	–5	5	–5x	5	µA
V_{IL}	Input Low Voltage			–0.5(1)	0.8	–0.5(1)	0.8	V
V_{IH}	Input High Voltage			2.2	6.0	2.2	6.0	V
V_{OL}	Output Low Voltage	I_{OL} = 8 mA, V_{CC} = Min. I_{OL} = 10 mA, V_{CC} = Min.		— —	0.4 0.5	— —	0.4 0.5	V V
V_{OH}	Output High Voltage	I_{OH} = –4 mA, V_{CC} = Min.		2.4	—	2.4	—	V

NOTE: 1. V_{IL}(min) = –3.0V for pulse width less than 20 ns.

Power Supply Characteristics

Symbol	Parameter	Power	-15 Com'l	-15 Ind.	-17 Com'l	-17 Ind.	-20 Com'l	-20 Ind.	-25 Com'l	-25 Ind.	Unit
I_{CC}	Operating Current $\overline{CE}$ = V_{IL}	SA	280	285	270	280	250	260	220	230	mA
	f = f_{MAX} = $1/t_{RC}$ V_{CC} = Max. I_{OUT} = 0 mA	LA	240	250	230	240	210	220	180	190	mA
I_{SB}	Standby Current $\overline{CE}$ = V_{IH}	SA	130	140	120	130	110	120	100	110	mA
	f = f_{MAX} = $1/t_{RC}$ V_{CC} = Max.	LA	100	110	90	100	80	90	70	80	mA
I_{SB1}	Full Standby Current $\overline{CE}$ ≥ V_{HC}	SA	40	40	40	40	40	40	40	40	mA
	f = 0 V_{CC} = Max., V_{IN} ≥ V_{CC} – 0.2V or ≤ 0.2V	LA	20	20	20	20	20	20	20	20	mA

NOTE:All values are maximum guaranteed values.
V_{LC} ≤ 0.2V, V_{HC} ≥ V_{CC} – 0.2V.

Capacitance[1] (T_A = +25°C, f = 1.0 MHz)

Symbol	Parameter	Max.	Unit
C_{IN}	Input Capacitance	8	pF
C_{OUT}	Output Capacitance	8	pF

NOTE: 1. This parameter is determined by device characterization but is not production tested.

AC Test Conditions

Input Pulse Levels	V_{SS} to 3.0V
Input rise and fall times	3 ns
Input timing reference levels	1.5V
Output reference levels	1.5V
Output load	See Figures 1 and 2

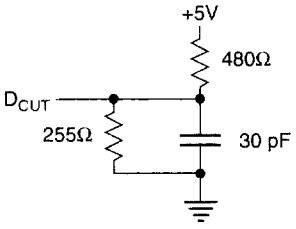


Figure 1. Output Load Equivalent

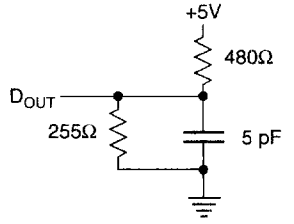
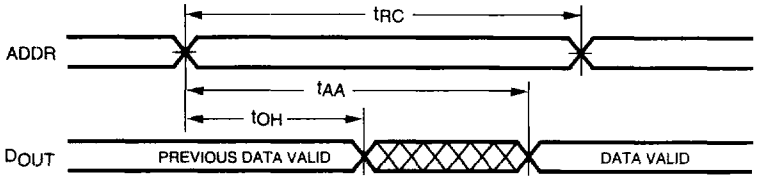
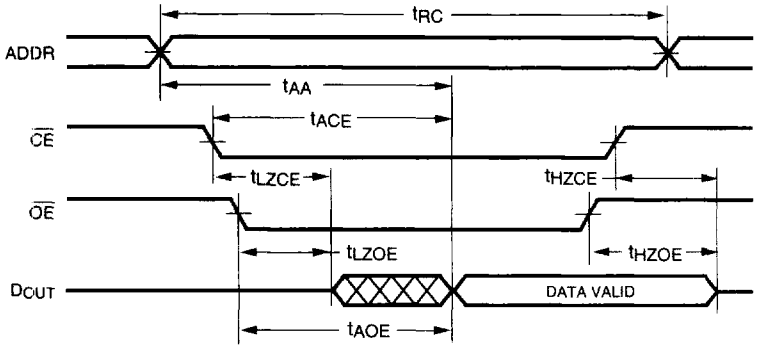


Figure 2. Output Load Equivalent (for t_{LZCE}, t_{HZCE}, t_{LZWE}, t_{HZWE}, t_{LZOE}, t_{HZOE})

Read Cycle No. 1[6, 7]



Read Cycle No. 2[3, 6, 8]

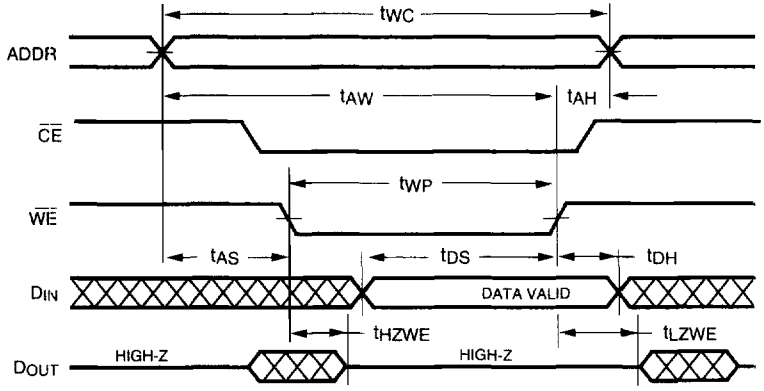


AC Electrical Characteristics

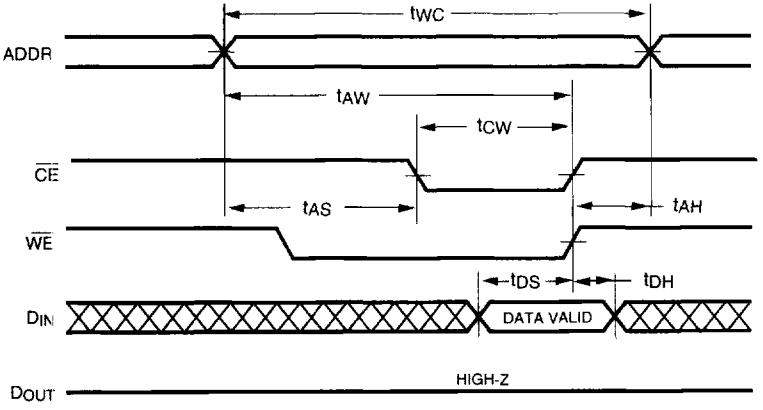
Description		-15[8]		-17[8]		-20		-25		
READ Cycle	**Symbol**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
READ cycle time	t_{RC}	15		17		20		25		ns
Address access time	t_{AA}		15		17		20		25	ns
Chip enable access time	t_{ACE}		15		17		20		25	ns
Output hold from address change	t_{OH}	5		5		5		5		ns
Chip enable to output in low Z[2,4]	t_{LZCE}	5		5		5		5		ns
Chip disable to output in high Z[2,3,4]	t_{HZCE}		6		7		8		10	ns
Chip enable to power up time[4]	t_{PU}	0		0		0		0		ns
Chip disable to power down time[4]	t_{PD}		15		17		20		25	ns
Output enable access time	t_{AOE}		6		7		8		10	ns
Output enable to output in low Z[2,4]	t_{LZOE}	0		0		0		0		ns
Output disable to output in high Z[2,4]	t_{HZOE}		6		7		8		10	ns

Notes referenced are after Data Retention Table.

Write Cycle No. 1 (Write Enable Controlled)



Write Cycle No. 2 (Chip Enable Controlled)

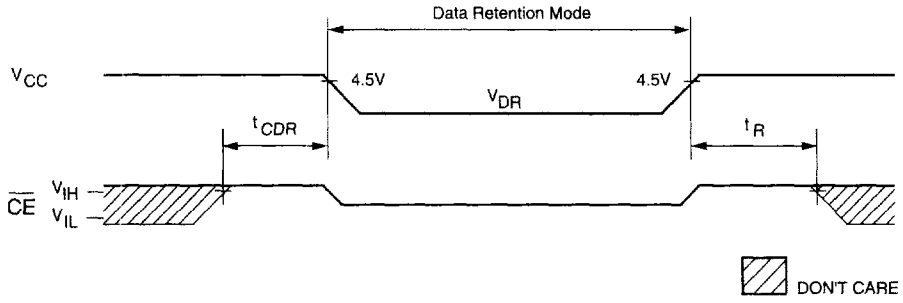


AC Electrical Characteristics

Description		-15[8]		-17[8]		-20		-25		
WRITE Cycle	**Symbol**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
WRITE cycle time	t_{WC}	15		17		20		25		ns
Chip enable to end of write	t_{CW}	12		15		15		20		ns
Address valid to end of write	t_{AW}	12		15		15		20		ns
Address setup time	t_{AS}	0		0		0		0		ns
Address hold from end of write	t_{AH}	0		0		0		0		ns
Write pulse width	t_{WP}	11		12		12		20		ns
Data setup time	t_{DS}	8		9		10		15		ns
Data hold time	t_{DH}	0		0		0		0		ns
Write disable to output in low Z[2,3]	t_{LZWE}	0		0		0		0		ns
Write enable to output in high Z[2,3]	t_{HZWE}		6		7		8		10	ns

Notes referenced are after Data Retention Table.

Low V_{CC} Data Retention Waveform



Data Retention Electrical Characteristics (LA Version Only)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
V_{DR}	V_{CC} for Retention Data			2	—	—	V
I_{CCDR}	Data Retention Current	$\overline{CE} \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ or $\leq 0.2V$	V_{CC} = 2V Com'l	—	—	1.0	mA
			V_{CC} = 3V Com'l	—	—	1.5	mA
t_{CDR}	Chip Deselect to Data Retention Time			0	—	—	ns
t_R[4]	Operation Recovery Time			t_{RC}[5]	—	—	ns

NOTES: (For three previous Electrical Characteristics tables)
1. –55°C to + 125°C temperature range only.
2. The parameter is tested with C_L = 5 pF as shown in Figure 2. Transition is measured ±200 mV from steady state voltage.
3. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}.
4. This parameter is sampled.
5. t_{RC} = Read cycle time.
6. $\overline{WE}$ is high for a READ cycle.
7. The device is continuously selected. Chip Enable is held in its active state.
8. V_{CC} = 5V ± 5%.

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Ordering Information